

## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	300	V
Collector-Emitter Voltage	V <sub>CEO</sub>	300	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	Ic	500	mA
Base Current	I <sub>B</sub>	100	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Discipation	(Note 6)	D-	2	W	
Power Dissipation	(Note 7)	P <sub>D</sub>	1	VV	
Thermal Decistores, Junction to Ambient	(Note 6)	D	62	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>θJA</sub>	125	C/VV	
Thermal Resistance, Junction to Leads (Note 8)		$R_{\theta JL}$	19.4	°C/W	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C	

# ESD Ratings (Note 9)

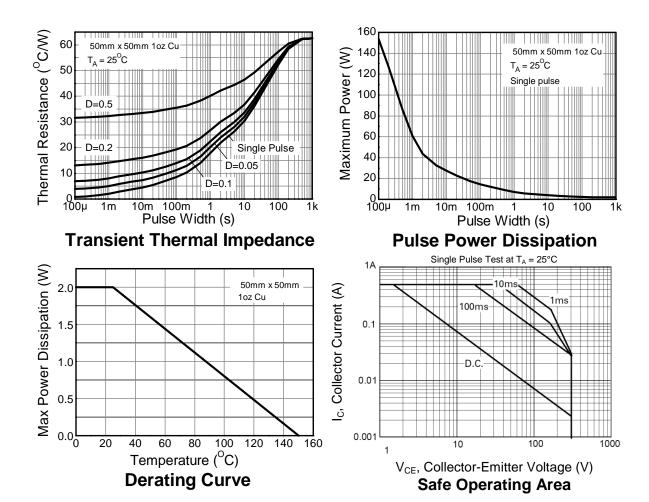
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the collector lead on 50mm x 50mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### **Thermal Characteristics and Derating Information**





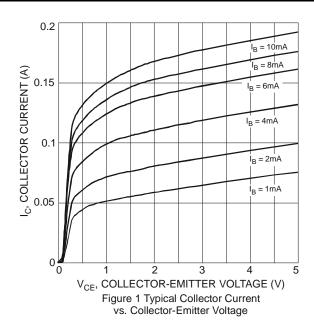
#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

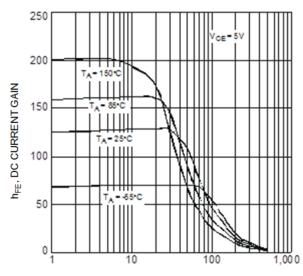
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS	OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	300	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	300	_	_	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	_	_	V	$I_E = 100\mu A$
Collector-Base Cut-off Current	I <sub>CBO</sub>	_	_	0.1	μΑ	V <sub>CB</sub> = 200V
Emitter-Base Cut-off Current	I <sub>EBO</sub>	_	_	0.1	μΑ	V <sub>EB</sub> = 6V
ON CHARACTERISTICS (Note 10)						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	_	0.5	V	$I_C = 20$ mA, $I_B = 2$ mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	_	0.9	V	$I_C = 20$ mA, $I_B = 2$ mA
		25	_	_		$I_C = 1mA, V_{CE} = 10V$
Static Forward Current Transfer Ratio	$h_{FE}$	40	_	_	l —	$I_C = 10mA, V_{CE} = 10V$
		40	_	_		$I_C = 30mA, V_{CE} = 10V$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f <sub>T</sub>	50	_	_	MHz	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 20V f = 100MHz
Output Capacitance	C <sub>OBO</sub>			3	pF	V <sub>CB</sub> = 20V, f = 1MHz

Note:

10. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.

# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





I<sub>C</sub>, COLLECTOR CURRENT (mA)
Figure 2 Typical DC Current Gain vs. Collector Current



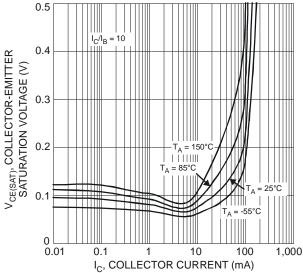


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

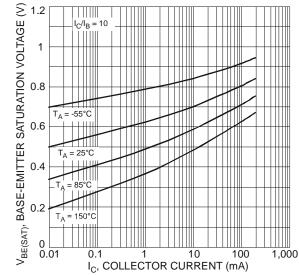


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

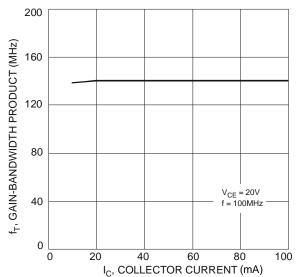


Figure 7 Typical Gain-Bandwidth Product vs. Collector Current

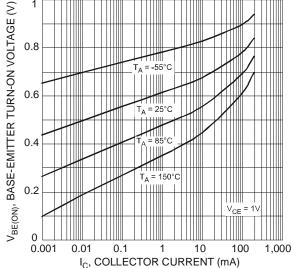


Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

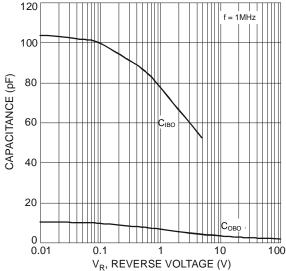


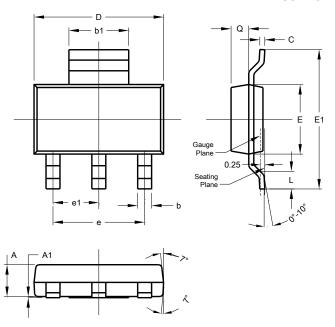
Figure 6 Typical Capacitance Characteristics



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223

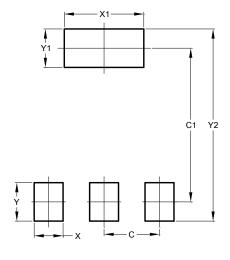


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT223**



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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